

IRF8721PbF

HEXFET® Power MOSFET

Applications

- Control MOSFET of Sync-Buck Converters used for Notebook Processor Power
- Control MOSFET for Isolated DC-DC Converters in Networking Systems

Benefits

- Very Low Gate Charge
- Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- 20V V_{GS} Max. Gate Rating
- Lead-Free

Description

The IRF8721PbF incorporates the latest HEXFET Power MOSFET Silicon Technology into the industry standard SO-8 package. The IRF8721PbF has been optimized for parameters that are critical in synchronous buck operation including $R_{ds(on)}$ and gate charge to reduce both conduction and switching losses. The reduced total losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors for Notebook and Netcom applications.

Absolute Maximum Ratings

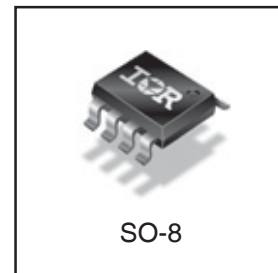
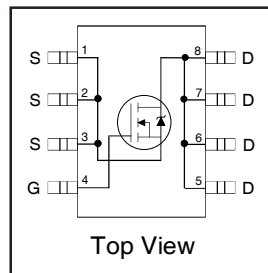
	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	14	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	11	
I_{DM}	Pulsed Drain Current ①	110	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	2.5	W
$P_D @ T_A = 70^\circ\text{C}$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④⑤	—	50	

Notes ① through ⑤ are on page 9

V_{DSS}	$R_{DS(on)}$ max	Qg
30V	8.5mΩ @ $V_{GS} = 10\text{V}$	8.3nC



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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

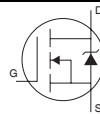
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.021	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.9	8.5	m Ω	$V_{GS} = 10V, I_D = 14A$ ③
		—	10.6	12.5		$V_{GS} = 4.5V, I_D = 11A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	—	2.35	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.2	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
gfs	Forward Transconductance	27	—	—	S	$V_{DS} = 15V, I_D = 11A$
Q_g	Total Gate Charge	—	8.3	12	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 11A$ See Fig. 16a and 16b
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	2.0	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	1.0	—		
Q_{gd}	Gate-to-Drain Charge	—	3.2	—		
Q_{godr}	Gate Charge Overdrive	—	2.0	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	4.2	—		
Q_{oss}	Output Charge	—	5.0	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	1.8	3.0	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	8.2	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ $I_D = 11A$ $R_G = 1.8\Omega$ See Fig. 15a
t_r	Rise Time	—	11	—		
$t_{d(off)}$	Turn-Off Delay Time	—	8.1	—		
t_f	Fall Time	—	7.0	—		
C_{iss}	Input Capacitance	—	1040	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	229	—		
C_{riss}	Reverse Transfer Capacitance	—	114	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	68	mJ
I_{AR}	Avalanche Current ①	—	11	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	112		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	14	21	ns	$T_J = 25^\circ\text{C}, I_F = 11A, V_{DD} = 15V$
Q_{rr}	Reverse Recovery Charge	—	15	23	nC	$di/dt = 300A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



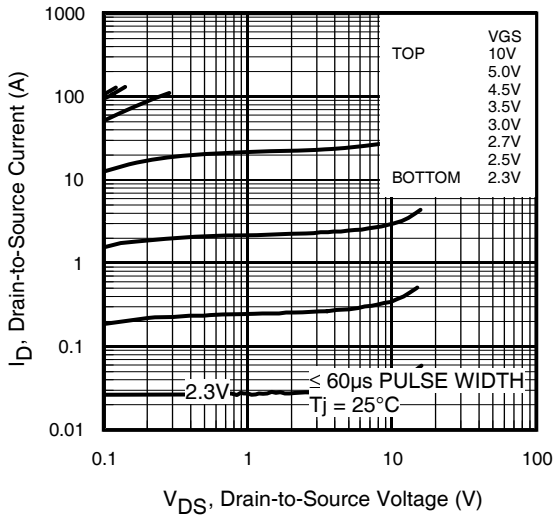


Fig 1. Typical Output Characteristics

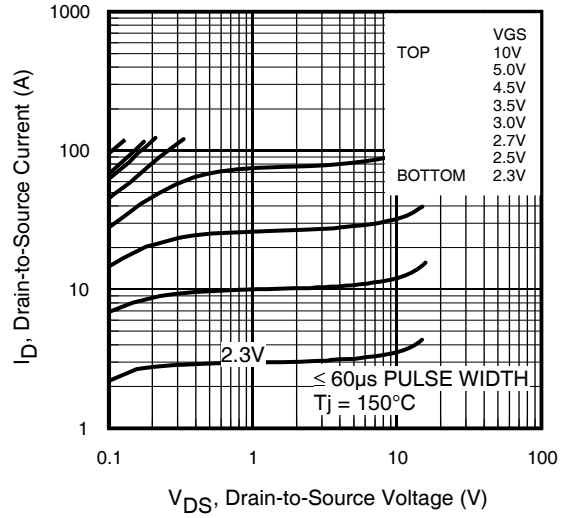


Fig 2. Typical Output Characteristics

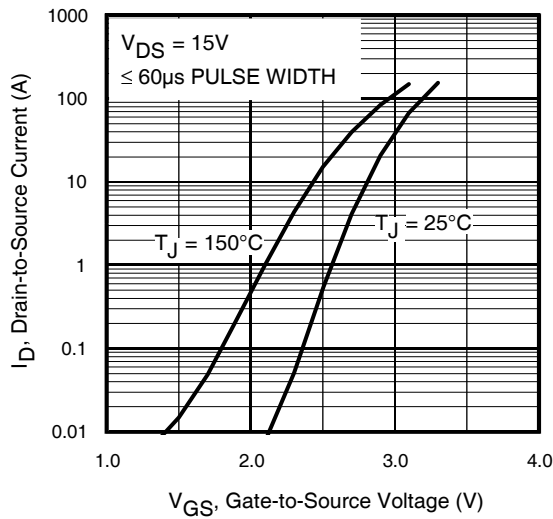


Fig 3. Typical Transfer Characteristics

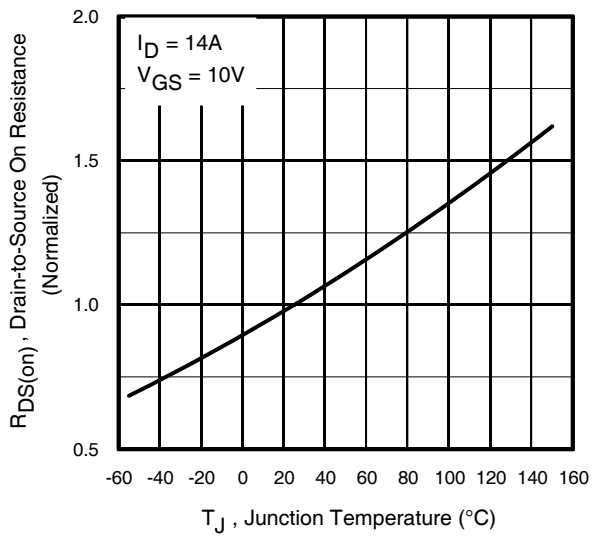


Fig 4. Normalized On-Resistance Vs. Temperature

IRF8721PbF

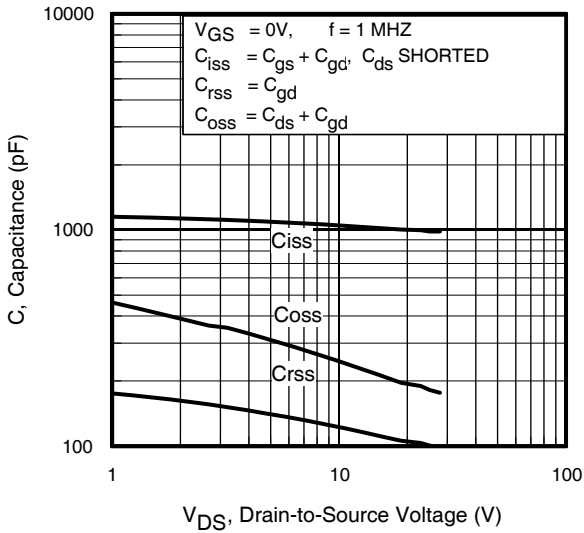


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

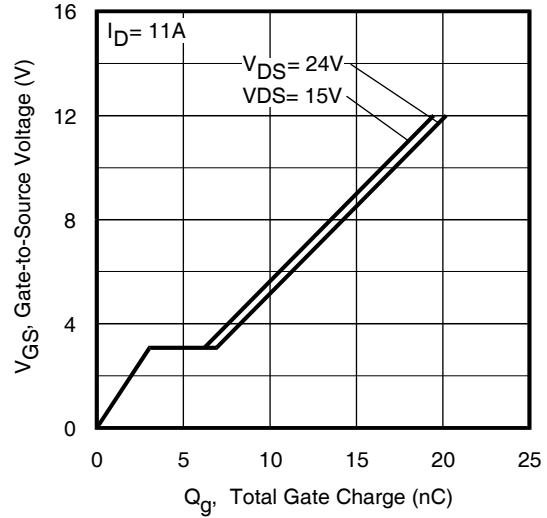


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

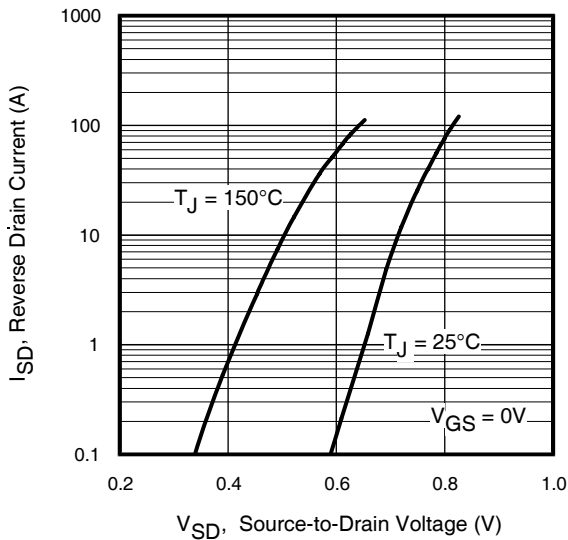


Fig 7. Typical Source-Drain Diode Forward Voltage

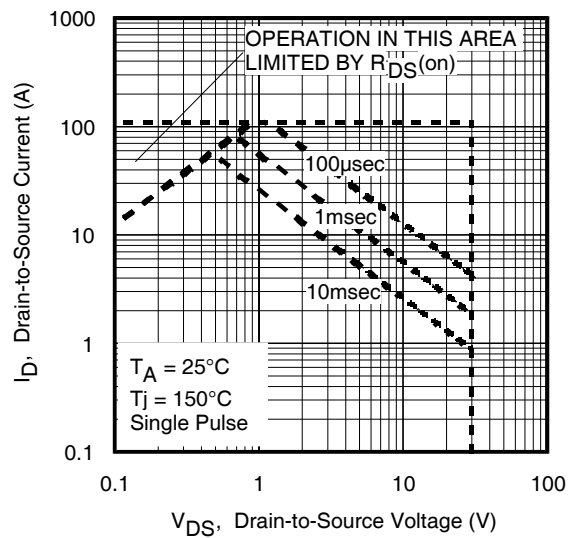


Fig 8. Maximum Safe Operating Area

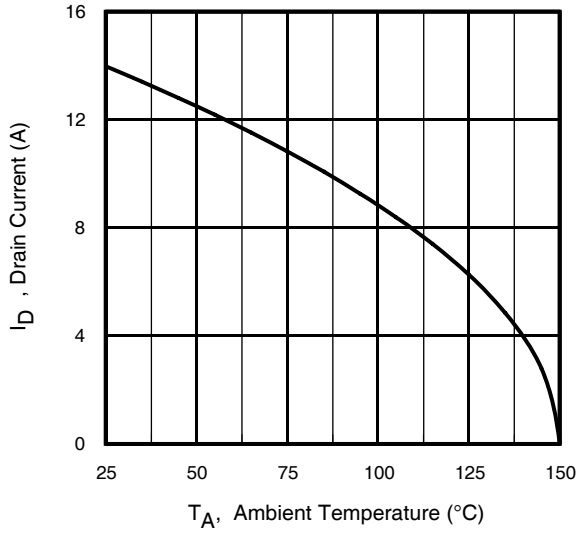


Fig 9. Maximum Drain Current Vs. Case Temperature

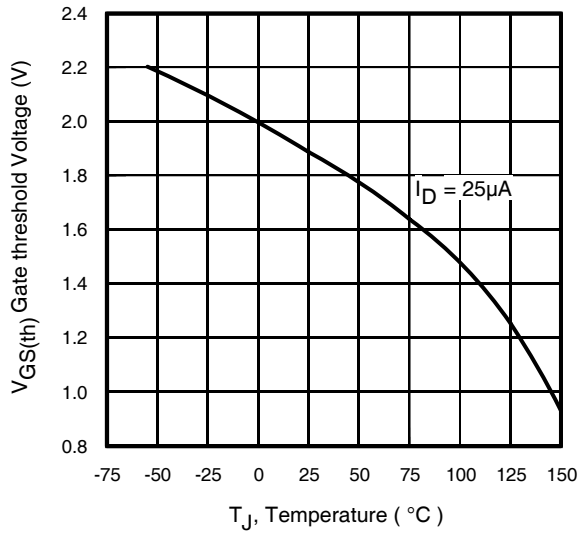


Fig 10. Threshold Voltage Vs. Temperature

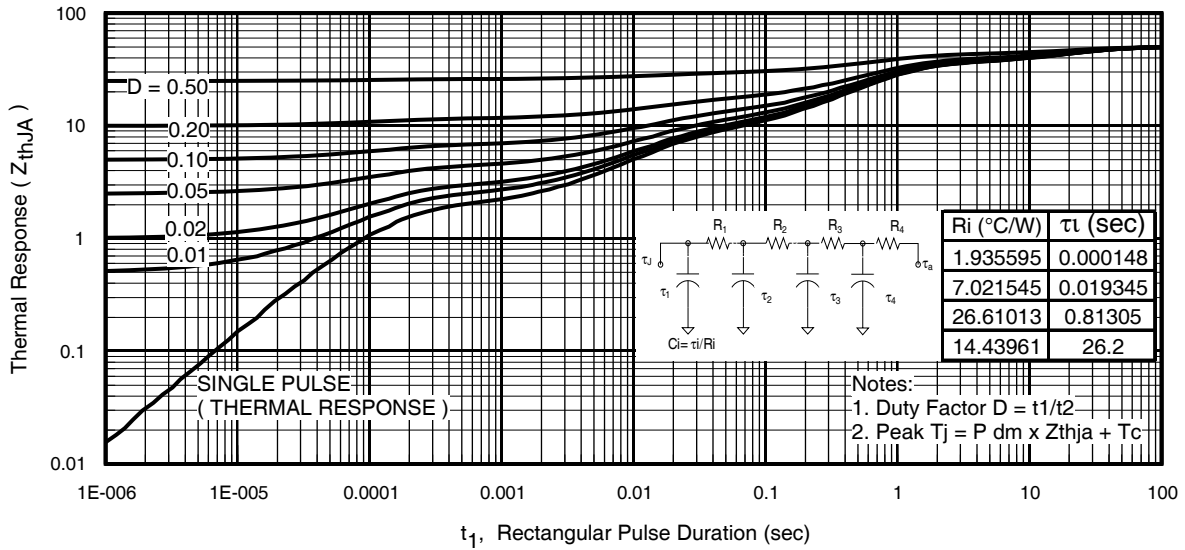


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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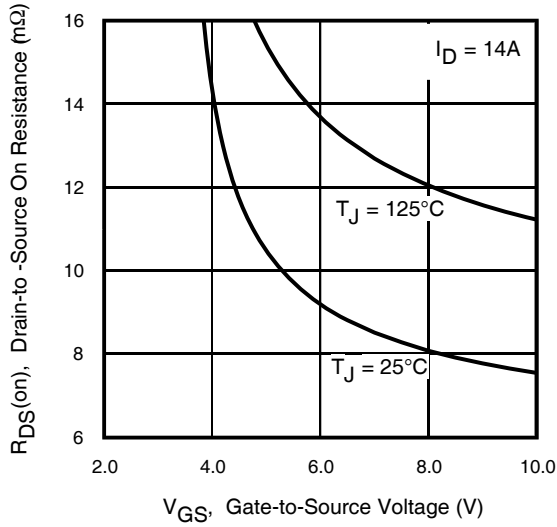


Fig 12. On-Resistance vs. Gate Voltage

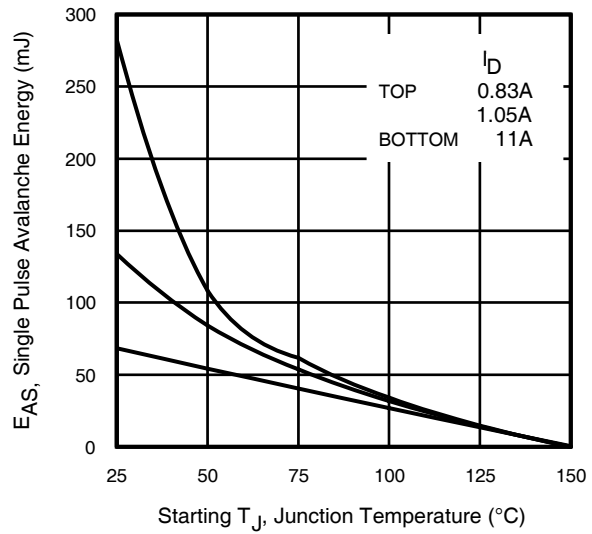


Fig 13. Maximum Avalanche Energy vs. Drain Current

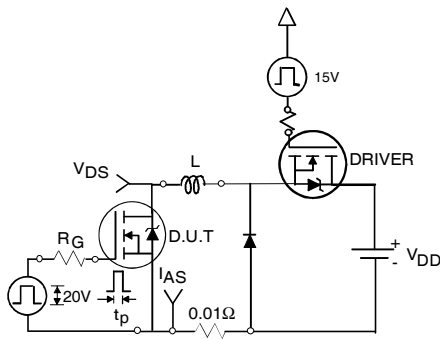


Fig 14a. Unclamped Inductive Test Circuit

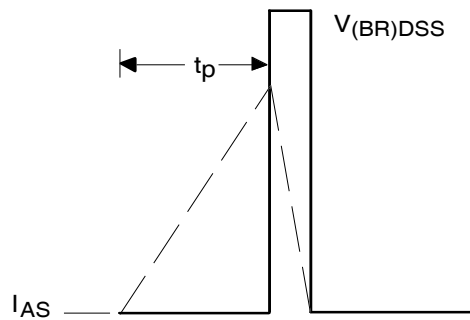


Fig 14b. Unclamped Inductive Waveforms

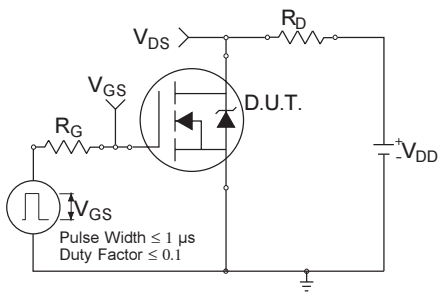


Fig 15a. Switching Time Test Circuit

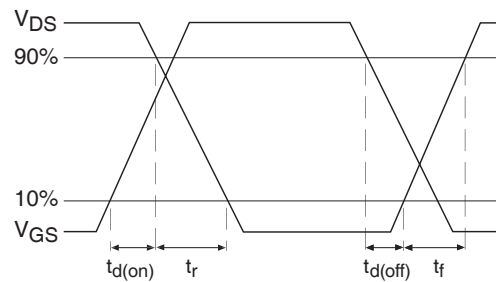


Fig 15b. Switching Time Waveforms

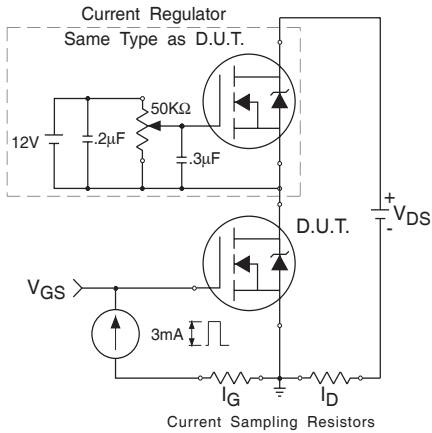


Fig 16a. Gate Charge Test Circuit

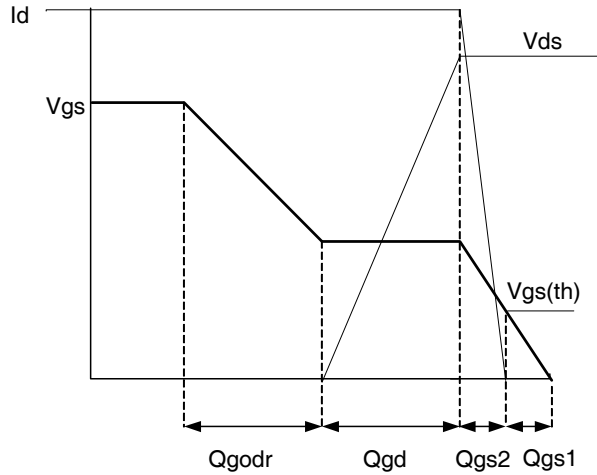
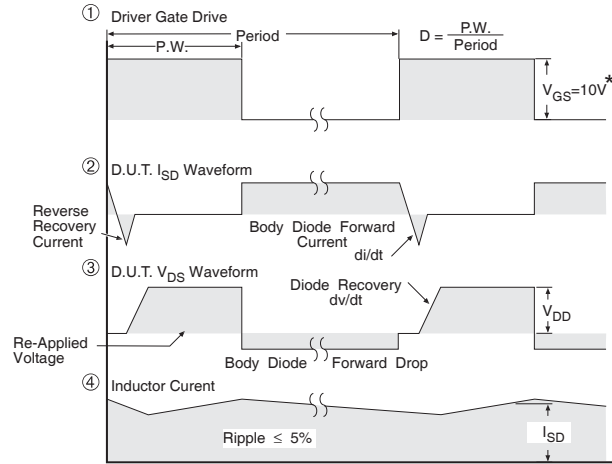
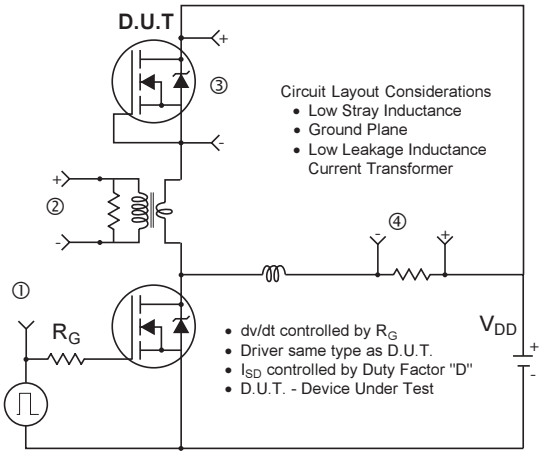


Fig 16b. Gate Charge Waveform



* $V_{GS} = 5V$ for Logic Level Devices

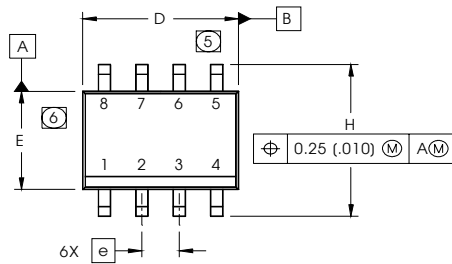
Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

IRF8721PbF

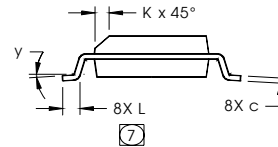
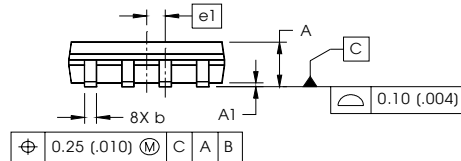
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SO-8 Package Outline

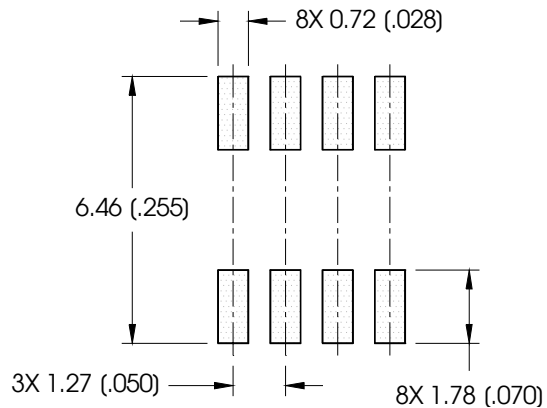
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



FOOTPRINT

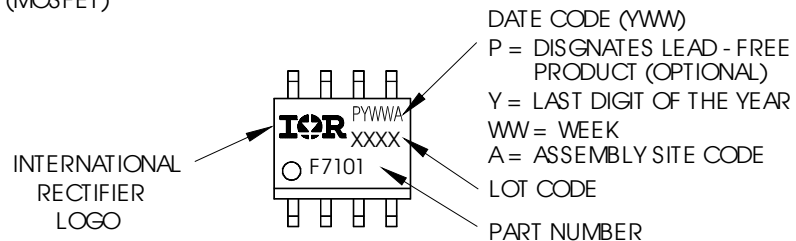


NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

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